

P-Channel MOSFET

General Description

The WSK42P10 is the highest performance trench P-Channel MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WSK42P10 meet the RoHS and Green Product requirement,100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline

Absolute Maximum Ratings

- 100% EAS Guaranteed
- Green Device Available

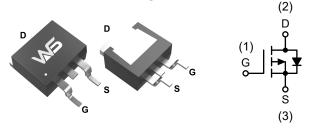
Product Summery

BV _{DSS}	R _{DSON}	I _D
-100V	78mΩ	-42A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

TO-263-2L Pin Configuration



Symbol Parameter Rating Units Drain-Source Voltage -100 V_{DS} V v Gate-Source Voltage ± 20 V_{GS} Continuous Drain Current, -V_{GS} @ -10V¹ I_D@T_C=25℃ -42 А Continuous Drain Current, -V_{GS} @ -10V¹ -19 I_D@T_C=100℃ А -75 Pulsed Drain Current² А I_{DM} Single Pulse Avalanche Energy³ 89 EAS mJ Avalanche Current -18.9 I_{AS} А 54 W P_D@T_C=25℃ Total Power Dissipation⁴ Storage Temperature Range -55 to 150 °C T_{STG} °C ΤJ **Operating Junction Temperature Range** -55 to 150

Thermal Data

Symbol	Parameter	Typ. Max.		Unit	
R _{0JA}	Thermal Resistance Junction-Ambient ¹		62	°C/W	
R _{θJC}	Thermal Resistance Junction-Case ¹		2.3	°C/W	



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Electrical Characteristics (TJ=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	-100			V
$\triangle BV_{DSS} / \triangle T_{J}$	BV _{DSS} Temperature Coefficient	Reference to 25 $^\circ\!\mathrm{C}$, I_D=-1mA		-0.021		V/℃
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-10V , I _D =-10A		78	95	mΩ
V _{GS(th)}	Gate Threshold Voltage		-1.2	-1.7	-2.5	V
$ riangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	VGS-VDS , IB2500A		4.08		mV/℃
I _{DSS}	Drain-Source Leakage Current	$V_{\text{DS}}\text{=-48V}$, $V_{\text{GS}}\text{=}0\text{V}$, $T_{\text{J}}\text{=}25^\circ\!\!\!\mathrm{C}$	1		1	uA
IDSS	Diam-Source Leakage Current	$V_{\text{DS}}\text{=-48V}$, $V_{\text{GS}}\text{=}0\text{V}$, $T_{\text{J}}\text{=}55^\circ\!\!\mathbb{C}$			5	uA
I _{GSS}	Gate-Source Leakage Current	V_{GS} = $\pm20V$, V_{DS} = $0V$			±100	nA
gfs	Forward Transconductance	V _{DS} =-10V , I _D =-10A		24		S
Qg	Total Gate Charge (-4.5V)			44		
Q _{gs}	Gate-Source Charge	V_{DS} =-50V , V_{GS} =-10V , I_{D} =-20A		9		nC
Q _{gd}	Gate-Drain Charge			6		
T _{d(on)}	Turn-On Delay Time			12		
Tr	Rise Time	V_{DD} =-30V , V_{GS} =-10V ,		27		20
T _{d(off)}	Turn-Off Delay Time	R_G =6 Ω , I_D =-10A ,RG=30 Ω .		79		ns
T _f	Fall Time			53		
C _{iss}	Input Capacitance			3029		
C _{oss}	Output Capacitance	V _{DS} =-30V , V _{GS} =0V , f=1MHz		129		pF
C _{rss}	Reverse Transfer Capacitance			76		

Guaranteed Avalanche Characteristics

Symbol	Parameter	Conditions		Тур.	Max.	Unit
EAS	Single Pulse Avalanche Energy 5	V _{DD} =-25V , L=0.5mH , I _{AS} =-10A	100			mJ

Diode Characteristics

Symbol	Parameter Conditions		Min.	Тур.	Max.	Unit
Is	Continuous Source Current ^{1,6}	$V_G=V_D=0V$, Force Current			-18	Α
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =-1A , T _J =25℃			-1.2	V

Note :

1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper, t \leq 10 sec.

2.The data tested by pulsed , pulse width $\leq 300 \text{us}$, duty cycle $\leq 2\%$

3.The EAS data shows Max. rating . The test condition is $V_{\text{DD}}\text{=-}25\text{V}, V_{\text{GS}}\text{=-}10\text{V}, \text{L=}0.5\text{mH}, \text{I}_{\text{AS}}\text{=-}18.9\text{A}$

4.The power dissipation is limited by 150 $^\circ\!\mathrm{C}$ junction temperature

5.The Min. value is 100% EAS tested guarantee.

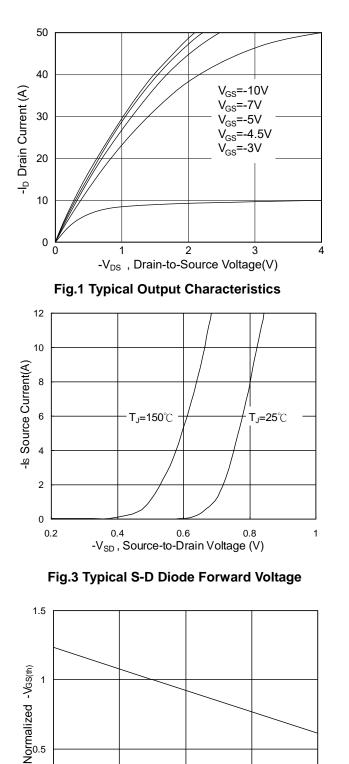
6.The data is theoretically the same as I_{D} and I_{DM} , in real applications , should be limited by total power dissipation.

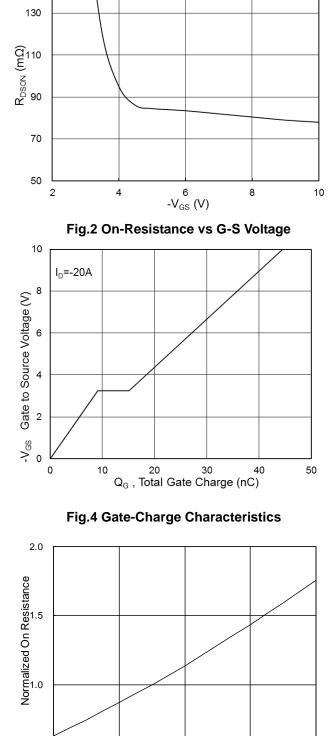


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I_D=-10A

Typical Characteristics





50

 T_J , Junction Temperature (°C)

Fig.6 Normalized R_{DSON} vs T_{J}

0

 T_{J}^{0} ,Junction Temperature ($^{100}_{C}$)

100

150

150

0.5

-50

150

0

-50



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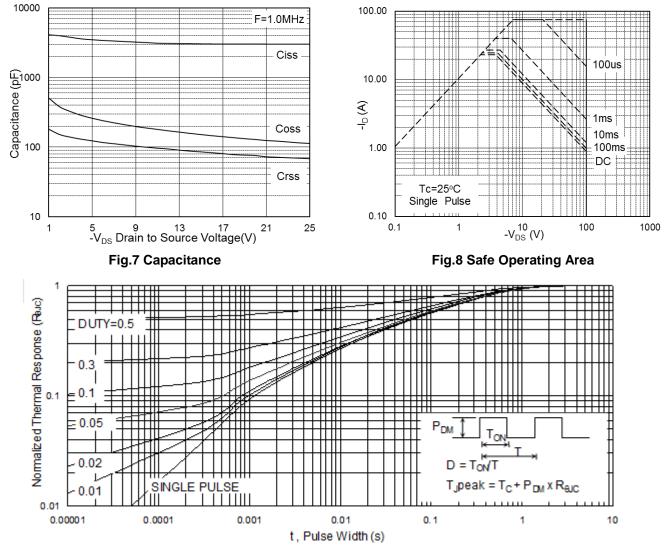
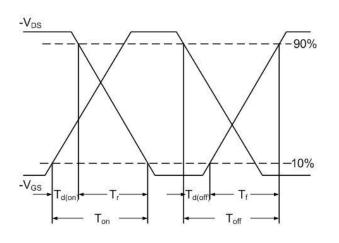


Fig.9 Normalized Maximum Transient Thermal Impedance





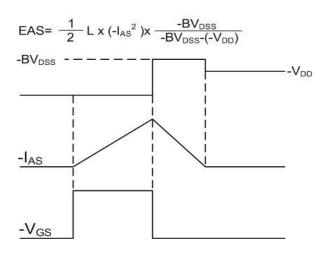
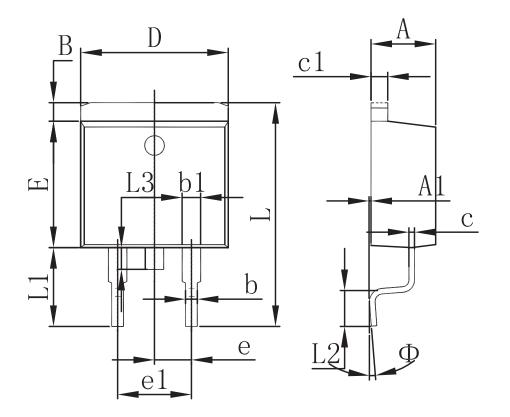


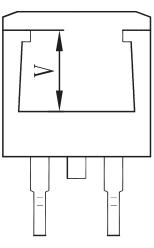
Fig.11 Unclamped Inductive Waveform



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Packaging information





Symbol	Dimensions Ir	n Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
A	4.470	4.670	0.176	0.184	
A1	0.000	0.150	0.000	0.006	
В	1.120	1.420	0.044	0.056	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.310	0.530	0.012	0.021	
c1	1.170	1.370	0.046	0.054	
D	10.010	10.310	0.394	0.406	
E	8.500	8.900	0.335	0.350	
е	2.540	TYP.	0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
L	14.940	15.500	0.588	0.610	
L1	4.950	5.450	0.195	0.215	
L2	2.340	2.740	0.092	0.108	
L3	1.300	1.700	0.051	0.067	
Φ	0°	8°	0°	8°	
V	5.600 REF. 0.220REF.			REF.	



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